| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 1 | 20770 | print with head | USPAT; US-PGPUB | 2003/10/28 11:59 |
| 2 | 486 | (print with head) and (drive with transistor) | USPAT; US-PGPUB | 2003/10/28 11:59 |
| 3 | 172 | ((print with head) and (drive with transistor)) and oxide | USPAT; US-PGPUB | 2003/10/28 11:59 |
| 4 | 150 | (((print with head) and (drive with transistor)) and oxide) and @ad<20020108 | USPAT; US-PGPUB | 2003/10/28 11:53 |
| 5 | 39038 | print with head | EPO; JPO; DERWENT; IBM_TDB | 2003/10/28 11:59 |
| 6 | 125 | (print with head) and (drive with transistor) | EPO; JPO; DERWENT; IBM_TDB | 2003/10/28 11:59 |
| 7 | 9 | ((print with head) and (drive with transistor)) and oxide | EPO; JPO; DERWENT; IBM_TDB | 2003/10/28 11:59 |

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| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 1 | 17 | (print with head) and transistor and oxide | EPO; JPO; DERWENT; IBM_TDB | 2003/10/28 14:14 |
| 2 | 452 | (print with head) and transistor and oxide | USPAT; US-PGPUB | 2003/10/28 14:14 |
| 3 | 384 | ((print with head) and transistor and oxide) and @ad<20020108 | USPAT; US-PGPUB | 2003/10/28 14:15 |

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| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 1 | 60518 | CMOS and @ad<20020108 | USPAT; US-PGPUB | 2003/10/28 10:04 |
| 2 | 48140 | (CMOS and @ad<20020108) and (source or drain) | USPAT; US-PGPUB | 2003/10/28 10:04 |
| 3 | 7666 | ((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide) | USPAT; US-PGPUB | 2003/10/28 10:05 |
| 4 | 7311 | (((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode) | USPAT; US-PGPUB | 2003/10/28 10:05 |
| 5 | 5773 | ((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors | USPAT; US-PGPUB | 2003/10/28 10:06 |
| 6 | 3639 | (((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting) | USPAT; US-PGPUB | 2003/10/28 10:06 |
| 7 | 3107 | ((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon | USPAT; US-PGPUB | 2003/10/28 10:07 |
| 8 | 1963 | (((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon) and (substrate with ((p adj type) or boron)) | USPAT; US-PGPUB | 2003/10/28 10:08 |
| 9 | 996 | ((((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon) and (substrate with ((p adj type) or boron))) and (second with transistor) | USPAT; US-PGPUB | 2003/10/28 10:08 |
| 10 | 735 | (((((((((CMOS and @ad<20020108) and (source or drain)) and ((depositing or deposited) with oxide)) and (gate or electrode)) and transistors) and (implant or implanting)) and polysilicon) and (substrate with ((p adj type) or boron))) and (second with transistor)) and (n with (doped or doping)) | USPAT; US-PGPUB | 2003/10/28 10:10 |

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